Accepted Manuscript

Electromagnetic separation of silicon carbide inclusions with aluminum penetration in silicon by imposition of supersonic frequency magnetic field

Dachuan Jiang, Shiqiang Qin, Pengting Li, Shuang Shi, Shutao Wen, Yi Tan

PII:	S0959-6526(17)30048-3
DOI:	10.1016/j.jclepro.2017.01.041
Reference:	JCLP 8788
To appear in:	Journal of Cleaner Production
Received Date:	12 October 2016
Revised Date:	28 November 2016
Accepted Date:	08 January 2017

Please cite this article as: Dachuan Jiang, Shiqiang Qin, Pengting Li, Shuang Shi, Shutao Wen, Yi Tan, Electromagnetic separation of silicon carbide inclusions with aluminum penetration in silicon by imposition of supersonic frequency magnetic field, *Journal of Cleaner Production* (2017), doi: 10.1016/j.jclepro.2017.01.041

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.



ACCEPTED MANUSCRIPT

Electromagnetic separation of silicon carbide inclusions with aluminum penetration in silicon by imposition of supersonic frequency magnetic field

Dachuan Jiang^{a,b}, Shiqiang Qin^{a,b}, Pengting Li^{a,b}, Shuang Shi^{a,b}, Shutao Wen^{a,b}, Yi Tan^{a,b,*}

^a School of Materials Science and Engineering, Dalian University of Technology, Dalian 116023,

China

^b Key Laboratory for Solar Energy Photovoltaic System of Liaoning Province, Dalian 116023, China Corresponding author at: School of Materials Science and Engineering, Dalian University of Technology, No. 2 Linggong Road, Ganjingzi District, Dalian City, Liaoning Province 116023, China. Tel./fax: +86 411 84707583. E-mail address: lnsolar@dlut.edu.cn (Yi Tan)

Abstract

A large amount of silicon in the form of silicon scraps is wasted annually in photovoltaic industry because of the presence of silicon carbide inclusions. Silicon carbide inclusions must be eliminated so that silicon scraps can be recycled. This study investigated the electromagnetic separation of silicon carbide inclusions in multicrystalline silicon by imposition of supersonic-frequency magnetic field. Silicon carbide particles tend to migrate to the ingot side and to the top and bottom of the central region of the ingot under increasing holding time. During separation process, the penetrating aluminum can react with silicon carbide and then dissolve some of the inclusions. In this work, the separation efficiency reaches up to 89.3% at a holding time of 45 min. This method is a potentially effective means of recycling silicon scraps.

Keywords: Silicon carbide; Silicon; Electromagnetic; Solar energy material

1. Introduction

With the recent development in photovoltaic industry, the need for solar-grade silicon has increased

Download English Version:

https://daneshyari.com/en/article/5481599

Download Persian Version:

https://daneshyari.com/article/5481599

Daneshyari.com